74HC2G14; 74HCT2G14

Dual inverting Schmitt trigger Rev. 2 — 14 March 2014

Product data sheet

1. **General description**

The 74HC2G14; 74HCT2G14 is a dual inverter with Schmitt-trigger inputs. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}. Schmitt trigger inputs transform slowly changing input signals into sharply defined jitter-free output signals.

Features and benefits 2.

- Wide supply voltage range from 2.0 V to 6.0 V
- Complies with JEDEC standard no. 7A
- Input levels:
 - ◆ For 74HC2G14: CMOS level
 - ◆ For 74HCT2G14: TTL level
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Unlimited input rise and fall times
- Multiple package options
- ESD protection:
 - HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

Applications 3.

- Wave and pulse shaper for highly noisy environments
- Astable multivibrators
- Monostable multivibrators



4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC2G14GW	-40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74HC2G14GV	–40 °C to +125 °C	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457
74HCT2G14GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74HCT2G14GV	-40 °C to +125 °C	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457

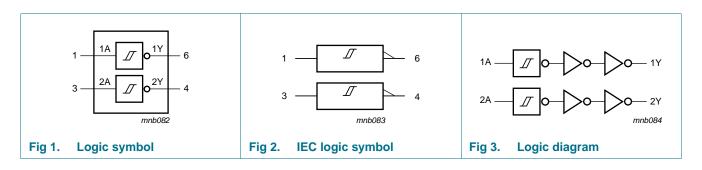
5. Marking

Table 2. Marking

Type number	Marking code ^[1]
74HC2G14GW	HK
74HC2G14GV	H14
74HCT2G14GW	тк
74HCT2G14GV	T14

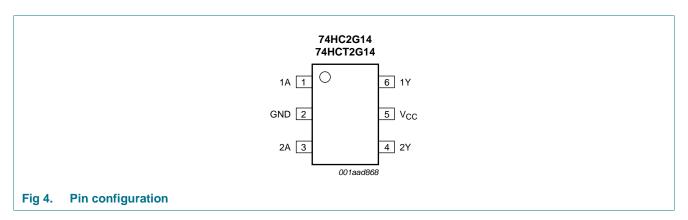
^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

6. Functional diagram



7. Pinning information

7.1 Pinning



7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V _{CC}	5	supply voltage
1Y	6	data output

8. Functional description

Table 4. Function table[1]

Input	Output
nA	nY
L	Н
Н	L

[1] H = HIGH voltage level;

L = LOW voltage level.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+7.0	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	<u>[1]</u>	-	±20	mA
I _{OK}	output clamping current	$V_{O} < -0.5 \text{ V or } V_{O} > V_{CC} + 0.5 \text{ V}$	<u>[1]</u>	-	±20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } V_{CC} + 0.5 \text{ V}$	<u>[1]</u>	-	±25	mA
I _{CC}	supply current		<u>[1]</u>	-	+50	mA
I _{GND}	ground current		<u>[1]</u>	-	-50	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation		[2]	-	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

10. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Type 74HC	2G14					
V _{CC}	supply voltage		2.0	5.0	6.0	V
VI	input voltage		0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Type 74HC	T2G14		,			
V _{CC}	supply voltage		4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C

^[2] For SC-88 and SC-74 packages: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K.

11. Static characteristics

Table 7. Static characteristics for 74HC2G14

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 25	°C		,		,	'
V _{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	V
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.18	4.32	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.68	5.81	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	V
		$I_O = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	V
l _l	input leakage current	$V_I = GND \text{ or } V_{CC}; V_{CC} = 6.0 \text{ V}$	-	-	±0.1	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \mu A;$	-	-	1.0	μΑ
		V _{CC} = 6.0 V				
Cı	input capacitance		-	2.0	-	pF
T _{amb} = -40) °C to +85 °C	'				1
V _{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	-	-	V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	-	-	V
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	-	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V};$	5.63	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.33	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	-	0.33	V
l _l	input leakage current	$V_I = GND \text{ or } V_{CC}; V_{CC} = 6.0 \text{ V}$	-	-	±1.0	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \mu\text{A};$ $V_{CC} = 6.0 V$	-	-	10.0	μΑ

 Table 7.
 Static characteristics for 74HC2G14 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -40) °C to +125 °C					
V _{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	-	-	V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	-	-	V
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.7	-	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V};$	5.2	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	-	0.1	V
		$I_{O} = 20 \mu A; V_{CC} = 4.5 V$	-	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	-	0.1	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	-	0.4	V
I _I	input leakage current	$V_I = GND \text{ or } V_{CC}; V_{CC} = 6.0 \text{ V}$	-	-	±1.0	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \mu A;$	-	-	20.0	μΑ
		$V_{CC} = 6.0 \text{ V}$				

Table 8. Static characteristics for 74HCT2G14

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 25 °	°C	'				
V _{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.18	4.32	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	V
II	input leakage current	$V_I = GND \text{ or } V_{CC}; V_{CC} = 5.5 \text{ V}$	-	-	±0.1	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 μ A; V_{CC} = 5.5 V	-	-	1.0	μА
Δl _{CC}	additional supply current	$V_I = V_{CC} - 2.1 \text{ V};$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}; I_O = 0 \mu\text{A}$	-	-	300	μΑ
Cı	input capacitance		-	2.0	-	pF

 Table 8.
 Static characteristics for 74HCT2G14 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -40) °C to +85 °C	,			,	
V _{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.33	V
l _l	input leakage current	$V_I = GND \text{ or } V_{CC}; V_{CC} = 5.5 \text{ V}$	-	-	±1.0	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 μ A; V_{CC} = 5.5 V	-	-	10.0	μΑ
Δl _{CC}	additional supply current	$V_I = V_{CC} - 2.1 \text{ V};$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}; I_O = 0 \mu\text{A}$	-	-	375	μΑ
$T_{amb} = -40$) °C to +125 °C	'		<u> </u>		1
V _{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.7	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.4	V
I _I	input leakage current	$V_I = GND \text{ or } V_{CC}; V_{CC} = 5.5 \text{ V}$	-	-	±1.0	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 μ A; V_{CC} = 5.5 V	-	-	20.0	μΑ
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 2.1 \text{ V};$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}; I_O = 0 \mu\text{A}$	-	-	410	μΑ

12. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 6.

Symbol	Parameter	Conditions			25 °C		-40 °C to +125 °C			Unit
				Min	Тур	Max	Min	Max (85 °C)	Max (125 °C)	
74HC2G1	14									
t _{pd}	propagation delay	nA to nY; see Figure 5	<u>[1]</u>							
		$V_{CC} = 2.0 \text{ V}; C_L = 50 \text{ pF}$		-	53	125	-	155	190	ns
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	16	25	-	31	38	ns
		$V_{CC} = 6.0 \text{ V}; C_L = 50 \text{ pF}$		-	13	21	-	26	32	ns
t _t	transition time	nY; see Figure 5	[2]							
		$V_{CC} = 2.0 \text{ V}; C_L = 50 \text{ pF}$		-	20	75	-	95	110	ns
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	7	15	-	19	22	ns
		$V_{CC} = 6.0 \text{ V}; C_L = 50 \text{ pF}$		-	5	13	-	16	19	ns
C_{PD}	power dissipation capacitance	$V_I = GND$ to V_{CC}	[3]	-	10	-	-	-	-	pF
74HCT20	614									
t _{pd}	propagation delay	nA to nY; see Figure 5	<u>[1]</u>							
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	21	32	-	40	48	ns
t _t	transition time	nY; see Figure 5	[2]							
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	6	15	-	19	22	ns
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC} - 1.5 \text{ V}$	[3]	-	10	-	-	-	-	pF

^[1] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

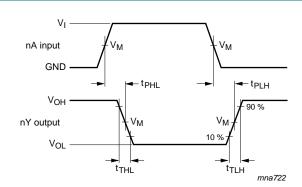
 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

^[2] t_t is the same as t_{TLH} and t_{THL}

13. Waveforms



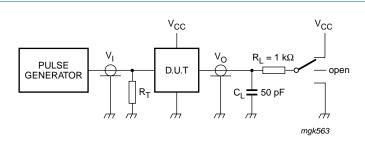
Measurement points are given in Table 10.

 $\ensuremath{V_{OL}}$ and $\ensuremath{V_{OH}}$ are typical voltage output levels that occur with the output load.

Fig 5. The data input (nA) to output (nY) propagation delays and output transition times

Table 10. Measurement points

Туре	Input	Output		
	V _M	VI	$t_r = t_f$	V _M
74HC2G14	0.5V _{CC}	GND to V _{CC}	6.0 ns	0.5V _{CC}
74HCT2G14	1.3 V	GND to 3.0 V	6.0 ns	1.3 V



Test data is given in Table 11.

Definitions test circuit:

 R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

Fig 6. Load circuitry for switching times

Table 11. Test data

Туре	Input	Test	
	VI	t _r , t _f	t _{PHL} , t _{PLH}
74HC2G14	GND to V _{CC}	6 ns	open
74HCT2G14	GND to 3.0 V	6 ns	open

74HC_HCT2G14

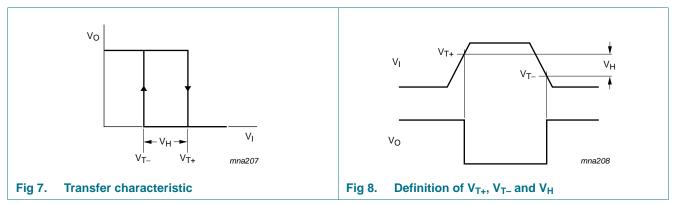
14. Transfer characteristics

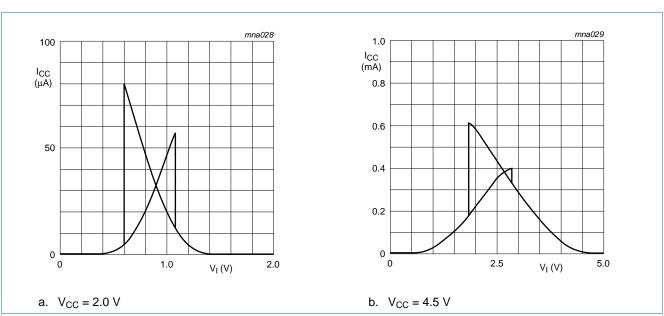
Table 12. Transfer characteristics

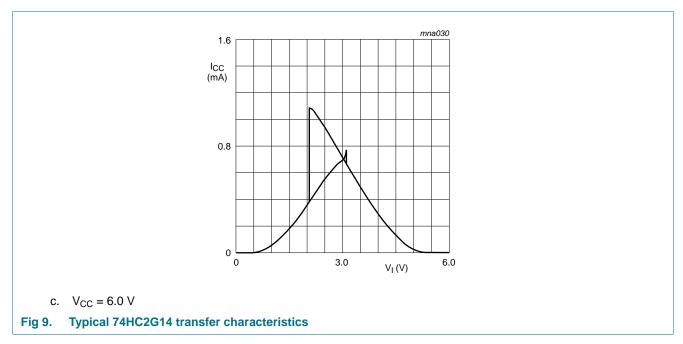
Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 6.

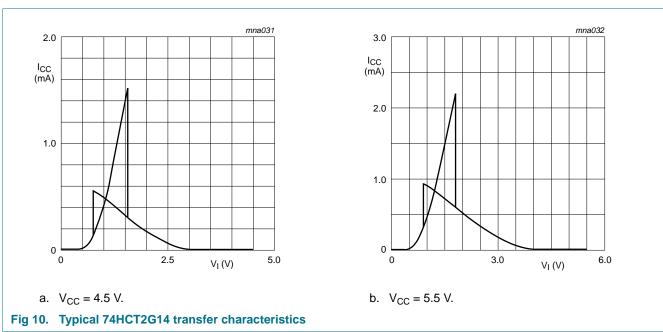
Symbol	Parameter	Conditions		25 °C		-40 °C to +125 °C			Unit	
			Min	Тур	Max	Min	Max (85 °C)	Max (125 °C)		
74HC2G	14									
	positive-going threshold voltage	see Figure 7, Figure 8								
		V _{CC} = 2.0 V	1.00	1.18	1.50	1.00	1.50	1.50	V	
		V _{CC} = 4.5 V	2.30	2.60	3.15	2.30	3.15	3.15	V	
		V _{CC} = 6.0 V	3.00	3.46	4.20	3.00	4.20	4.20	V	
V_{T-}	negative-going	see Figure 7, Figure 8								
	threshold voltage	V _{CC} = 2.0 V	0.30	0.60	0.90	0.30	0.90	0.90	V	
		V _{CC} = 4.5 V	1.13	1.47	2.00	1.13	2.00	2.00	V	
		V _{CC} = 6.0 V	1.50	2.06	2.60	1.50	2.60	2.60	V	
V _H hysteresis voltage	hysteresis voltage	(V _{T+} – V _{T-}); see <u>Figure 7</u> , <u>Figure 8</u> and <u>Figure 9</u>								
		V _{CC} = 2.0 V	0.30	0.60	1.00	0.30	1.00	1.00	V	
		V _{CC} = 4.5 V	0.60	1.13	1.40	0.60	1.40	1.40	V	
		V _{CC} = 6.0 V	0.80	1.40	1.70	0.80	1.70	1.70	V	
74HCT2	G14									
	positive-going threshold voltage	see Figure 7 and Figure 8								
		V _{CC} = 4.5 V	1.20	1.58	1.90	1.20	1.90	1.90	V	
		V _{CC} = 5.5 V	1.40	1.78	2.10	1.40	2.10	2.10	V	
	negative-going threshold voltage	see Figure 7 and Figure 8								
		V _{CC} = 4.5 V	0.50	0.87	1.20	0.50	1.20	1.20	V	
		V _{CC} = 5.5 V	0.60	1.11	1.40	0.60	1.40	1.40	V	
V _H	hysteresis voltage	(V _{T+} – V _{T-}); see <u>Figure 7</u> , <u>Figure 8</u> and <u>Figure 10</u>								
		V _{CC} = 4.5 V	0.40	0.71	-	0.40	-	-	V	
		V _{CC} = 5.5 V	0.40	0.67	-	0.40	-	-	V	

15. Waveforms transfer characteristics









16. Application information

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

 $P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC}$ where:

 P_{add} = additional power dissipation (μW);

 $f_i = input frequency (MHz);$

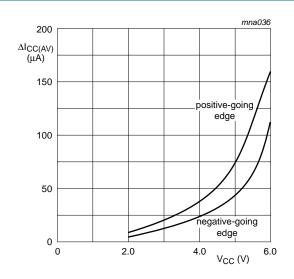
 t_r = input rise time (ns); 10 % to 90 %;

 t_f = input fall time (ns); 90 % to 10 %;

 $\Delta I_{CC(AV)}$ = average additional supply current (μA).

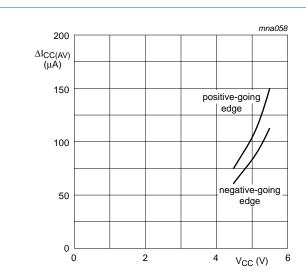
 $\Delta I_{CC(AV)}$ differs with positive or negative input transitions, as shown in <u>Figure 11</u> and <u>Figure 12</u>.

An example of a relaxation circuit using the 74HC2G14/74HCT2G14 is shown in Figure 13.



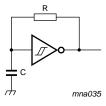
- (1) Positive-going edge.
- (2) Negative-going edge.

Fig 11. ΔI_{CC(AV)} as a function of V_{CC} for 74HC2G14; linear change of V_I between 0.1V_{CC} to 0.9V_{CC}



- (1) Positive-going edge.
- (2) Negative-going edge.

Fig 12. $\Delta I_{CC(AV)}$ as a function of V_{CC} for 74HCT2G14; linear change of V_I between 0.1 V_{CC} to 0.9 V_{CC}

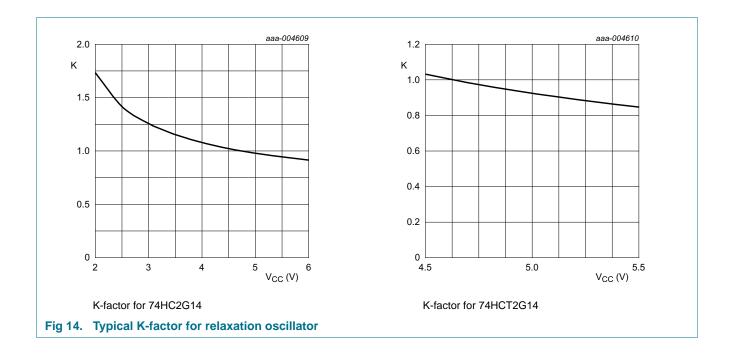


For 74HC2G14:
$$f = \frac{1}{T} \approx \frac{1}{0.8 \times RC}$$

For 74HCT2G14:
$$f = \frac{1}{T} \approx \frac{1}{0.67 \times RC}$$

For K-factor, see Figure 14

Fig 13. Relaxation oscillator



17. Package outline

Plastic surface-mounted package; 6 leads **SOT363** Α X = v M A ⊕ w M B е detail X **DIMENSIONS (mm are the original dimensions)** Α1 UNIT Α D Ε С Q е HΕ Lp v w у max 0.30 0.25 0.45 0.25 1.1 2.2 1.35 2.2 0.65 0.1 0.20 0.10 1.8 8.0 1.15 0.15 0.15 **REFERENCES EUROPEAN** OUTLINE ISSUE DATE VERSION **PROJECTION** JEDEC IEC **JEITA** 04-11-08 SOT363 SC-88 06-03-16

Fig 15. Package outline SOT363 (SC-88)

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Plastic surface-mounted package (TSOP6); 6 leads

SOT457

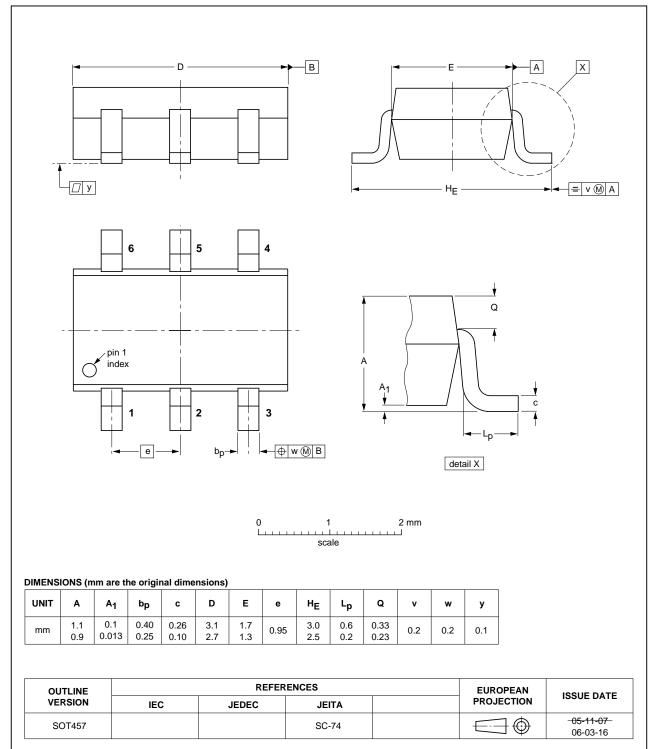


Fig 16. Package outline SOT457 (SC-74)

18. Abbreviations

Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
DUT	Device Under Test

19. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74HC_HCT2G14 v.2	20140314	Product data sheet	-	74HC_HCT2G14 v.1	
Modifications:	Figure 14 added (typical K-factor for relaxation oscillator).				
74HC_HCT2G14 v.1	20061011	Product data sheet	-	-	

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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